

# Bablu Mukherjee | Resume

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Experienced researcher with a demonstrated history of working in top research institute. **Electrical and material science engineer with a skill set in fabrication, nano-architectonics, process and application improvement, data analysis, and nanomaterial science engineering.** Interested in solid-state devices R&D for detectors, optical sensors, memory, and multifunctional device development.



**PERSONAL:** Name: Bablu Mukherjee

**Date of Birth:** 3<sup>rd</sup> January 1987, **Nationality:** Indian, **Gender & Marital Status:** Male & Married, **Languages Known:** English, Hindi & Bengali, **E-Mail:** [bablu.iitm@gmail.com](mailto:bablu.iitm@gmail.com)

## PROFILE SUMMARY:

- A semiconductor physicist and device engineer with almost 6+ years of hands-on experience of clean-room nanodevice fabrication and characterization. Experience in laboratory instrumentation and measurement techniques (**Opto-electronics, energy conversion, optical sensors**) and new device **application developments**.
- Excellent communication and writing skills, leadership & management skills, **raising independent project funding including project design, planning and execution**, managed cutting-edge R&D projects.

**CORE COMPETENCIES:** Nanotechnology | Material Science | Optoelectronics | Energy Conversion | Sensor

## RESEARCH & PROJECT MANAGEMENT EXPERIENCE:

**National Institute for Materials Science (NIMS) JSPS Fellow Nov. 2017 – Present**

- ✚ Interlayer Transition and Infrared Photodetection in MoTe<sub>2</sub>/ReS<sub>2</sub> *p-n* van der Heterostructures
- ✚ CMOS Technology Compatible Vertical p-Si/n-ReS<sub>2</sub> Efficient Near-Infrared Photodiode
- ✚ Laser Assist Non-Volatile Memory Devices Based on 2D Heterostructures

**Indian Institute of Technology (IIT), Bombay Institute Post-Doctoral Fellow Sep. 2015 – April 2017**

- ✚ Few Layer ReS<sub>2</sub> Plasmonic Phototransistor with High-Performance Optoelectronics
- ✚ Control of Two-dimensional Excitonic Light Emission *via* Periodic Structures and Applied Field

**The George Washington University (GWU) Post-Doctoral Scientist Mar. 2014 – Aug. 2015**

- ✚ Optical Properties and Extraction of Complex Electrical Permittivity of Monolayer MoS<sub>2</sub>
- ✚ Enhancing Optical Absorption and Scattering of Monolayer MoS<sub>2</sub> with Plasmonic Gold Nanoparticles

## TECHNICAL HIGHLIGHTS & SKILLS:

**Experimental Skill:** Fabrication and Analytical Techniques:

- ✚ Thin film deposition: Sputtering, CVD, PECVD, Atomic layer deposition (ALD), e-beam deposition.
- ✚ Lithography techniques: Electron beam lithography (EBL), Laser lithography, Photo-lithography.
- ✚ Spectroscopic analysis: Micro-Raman, XRD, XPS, micro-PL, differential reflectance spectroscopy.
- ✚ Electrical characterization: C-V, C-f, I-V, I-t, Hall measurement, small signal using lock-in amplifier.

**Simulation and Software Experiences:**

- ✚ Optical/Device tool: Wavenology-3D EM Wave Solver, Lumerical FDTD/Device, CST Studio, Comsol.
- ✚ Analysis tool: Matlab, Python data analysis, Microsoft Excel and Plotting tool: Origin, XPS peak fit 4.1.
- ✚ Designs: AutoCAD, Design CAD, Google Sketch Up.

## EDUCATION:

**National University of Singapore (NUS), Singapore: 31<sup>st</sup> Dec. 2013**

Doctor of Philosophy (Ph. D) in Experimental Nanoscience/Applied Physics

Title **Layered Chalcogenides Nanostructures: Synthesis, Characterisation and Optoelectrical Applications**

**Indian Institute of Technology (IIT) Madras, India: 31<sup>st</sup> July 2009**

Master of Science (M.Sc.) in Physics (*Specialization: Nanoscience and Nanotechnology*)

**University of Calcutta, Kolkata, West Bengal, India: 23<sup>rd</sup> July 2007**

Bachelor of Science (B. Sc.) in Physics Honours, (Ramakrishna Mission Residential College, Narendrapur)

## LEADERSHIP ACTIVITIES:

**VIT University, Vellore, TN, India May 2017 – Nov. 2017**

- ✚ **Assistant Professor** in Physics, School of Advanced Sciences. AGP 7,200. PB: 18,600 - 39,100
- ✚ **Engineering Physics (PHY 1701) Course (Theory + Laboratory)-** for 3 batches undergraduates

## PROFESSIONAL SCIENTIFIC ACTIVITIES:

- ✚ **Editorial Board Member:** Advances in Materials of Science Publishing Group, USA.
- ✚ **Fellow Member:** OSI (F1311), Optical Society of India, Japan Society of Applied Physics, JSAP (M040941)
- ✚ **Review / Editing:** Nanoscale, Applied Nanoscience, Plasmonics, IEEE Photonics, Applied Physics Letter
- ✚ **Volunteer:** The 3rd International Conference on Emerging Electronics (ICEE 2016), Dec. 2016
- ✚ **Advisor:** Mendeley, Elsevier for managing references and sharing research papers.

## AWARDS & ACHIEVEMENTS & CERTIFICATIONS:

- ✚ **Excellent Poster** Presentation Award in the MANA International Symposium 2019, Tsukuba, Japan
- ✚ Nominated for **Best Poster** Award in the 79th JSAP Autumn Meeting 2018, Nagoya Japan.
- ✚ **JSPS Postdoctoral Fellowship** at National Institute for Materials Science, NIMS, Tsukuba, JAPAN
- ✚ **DAAD Scholarship 2009** - Institute of Electronic Material and Devices (LUH)- Germany
- ✚ Ranked 57 in all India Joint Entrance Screening Test (**JEST 2009**) Examination
- ✚ Qualified Graduate Aptitude Test in Engineering (**GATE-2009**) in Physics (Percentile: 93.17)
- ✚ Certificate of merit for National top 1% in National Graduate Physics Examination **NGPE 2006-07**
- ✚ Certificate of completion in Microsoft Excel Advanced usage from UDEMY.

## PUBLICATIONS (#5 out of #13 FIRST AUTHOR) - PEER REVIEWED ARTICLES (Total #22):

1. **B. Mukherjee et al.** Nature Electronics, 2020 (Sub.), Laser Assist Multi-Level Nonvolatile Memory.
2. **B. Mukherjee et al.** ACS Photonics, 6, 2277, 2019, Enhanced Quantum Efficiency in Vertical ReS<sub>2</sub>/Si Photodiode
3. **B. Mukherjee et al.** Scientific Reports, 7, 41175, 2017, Exciton Emission Intensity Modulation of Monolayer MoS<sub>2</sub>
4. **B. Mukherjee et al.** ACS Appl. Mater. Interfaces, 5, 2013, 9594, NIR Photodetectors of Individual GeSe Nanosheet
5. **B. Mukherjee et al.** J. Material Chemistry, 22, 2012, 24882, Stepped-surfaced GeSe<sub>2</sub> with high-gain photoconductivity